

Earth Science Technology Conference 2003



Performance Assessment and Space Qualification of 808 nm Quasi-constant Wave Laser Diode Arrays

Mark Stephen - GSFC

Alex Vasilyev - SSAI

John Schafer - SSAI



OUTLINE



- Motivation
- Research goals and strategy
- Progress on characterization capability
- Future plans
- Conclusions



Motivation



- Recent laser missions (GLAS, MOLA) and upcoming missions (MLA, CALIPSO, DLA, etc.) employ Q-switched Nd:YAG lasers
- Efficient pumping of these lasers requires quasi-CW Laser Diode Arrays (LDA) emitting at 808 nm
- Need information on performance and reliability of these devices under space flight conditions.



Research Goals



- → Quantify effect of operational and environmental parameters
- → List of practices for handling, storage and operation
- → Predictive/screening capability
- → Improve reliability
- → Lessons learned for purchasing procedure



Environmental and Operational Parameters



Environment

- **→** Radiation
- → Vacuum
- → Vibration
- → Cleanliness
- → Aging

Operation

- → Optical Power
- → Electrical drive pulse width, shape, frequency, amplitude
- → Temperature
- → Power cycling



Research Strategy



- Characterize LDAs establish an initial baseline for individual array performance and status.
- Subject LDA to a form of stress environment and/or life test
 - Radiation
 - Vacuum
 - Life test
- Characterize LDA again quantify effect of the stressor
- Track changes and correlate to initial characterization or stressor

It is critical that our characterization be repeatable so changes we observe can be credited to stress parameter and not test error.



Environmental Monitoring Capabilities





ARTI HHPC-6 Particle Counter

- 0.3, 0.5, 0.7, 1.0, 2.0, 5.0 micron particles
- Humidity and Temperature



Electrical Characterization

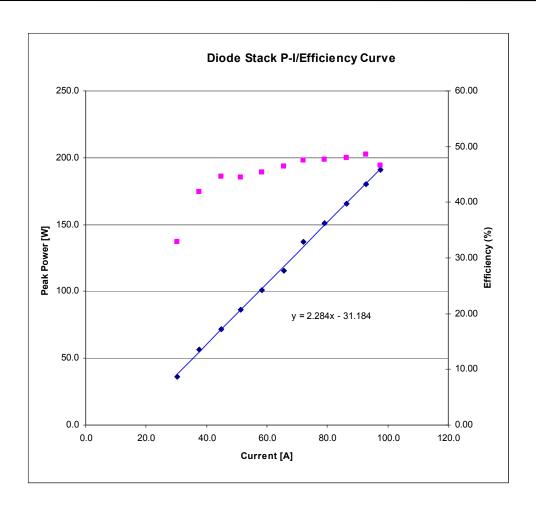


- Current (pulse width, amplitude, frequency, duty cycle)
- Voltage (pulse width, amplitude, frequency, duty cycle)
- Resistance
- Efficiency
- Lasing threshold



LDA Optical Power





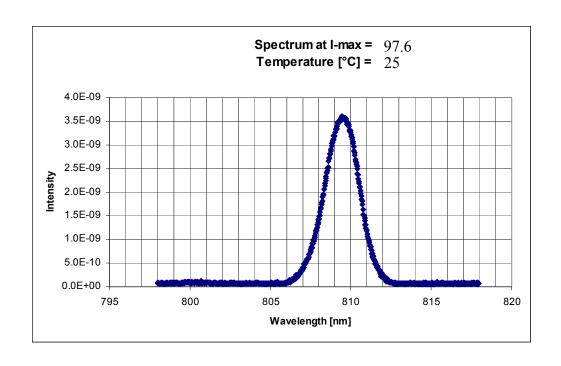






LDA Optical Spectrum





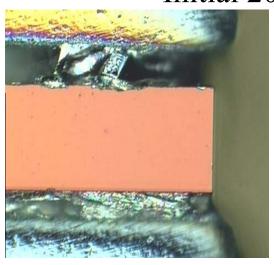
- Center wavelength 809.48 nm
- Width -2.33 nm

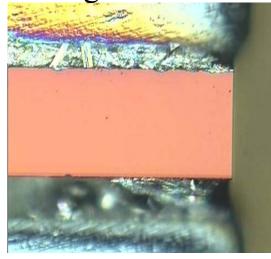


Microscope Inspection

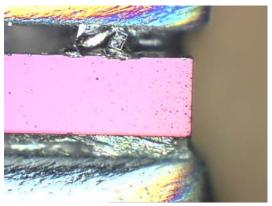


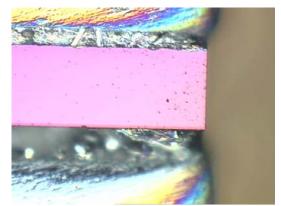
Initial 200x Diode Bar Images





Images after Indium contamination

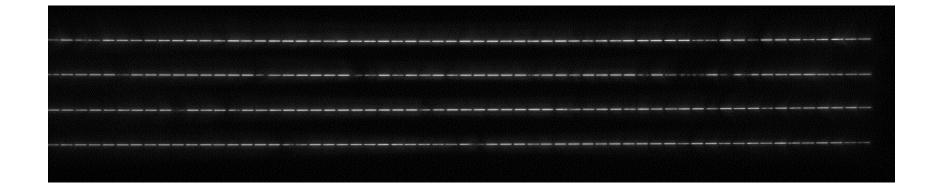






LDA Near Field Profile





Near field image of 4-bar LDA showing optical power distribution across facet operating at full power. One megapixel monochrome 10bit digital CCD camera

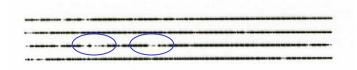


Infrared Inspection

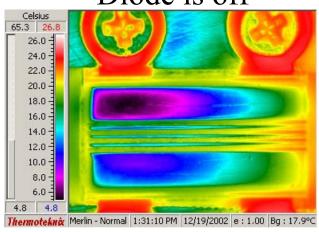




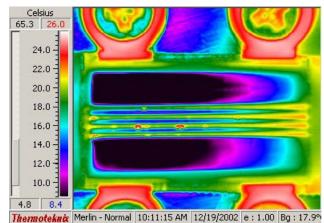
Near field image



Diode is off



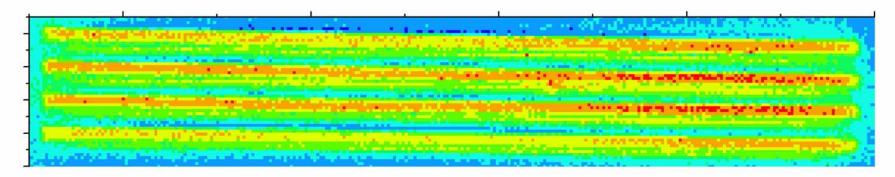
Diode is on



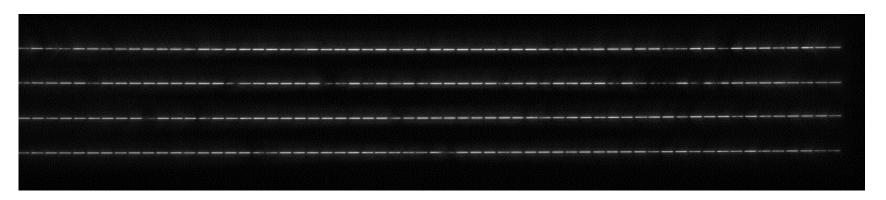


Comparison of Temperature profile and Near field emission





Infrared Profile of 4-bar LDA at 25 micron spatial resolution, 0.1 C temperature resolution

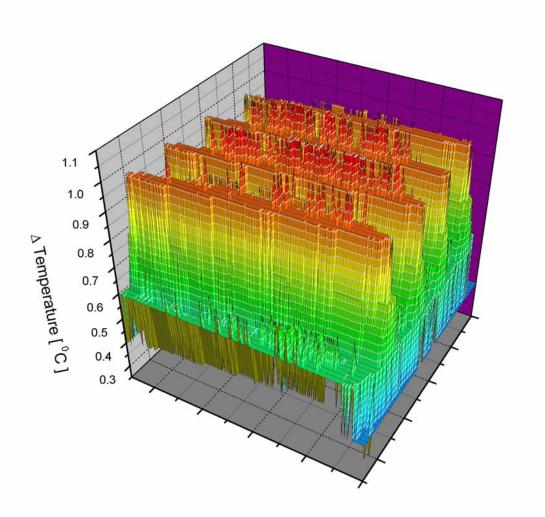


Near field emission of same LDA



Facet Heating of LDA during operation





Infrared image illustrating the temperature gradient between the LDA when it is powered on and off. Profile is attained by subtracting the IR image of the LDA which is off from the image when the LDA on.



Summary of Present Characterization Capabilities



Electrical properties

- current (width, shape, amplitude, frequency, duty cycle)
- voltage (width, shape, amplitude, frequency, duty cycle)
- resistance
- efficiency

Optical properties

- average optical power
- average spectrum
- near field image

Other

- infrared image with 25 micron resolution
- visible image
- 200X visible facet inspection



Future Work

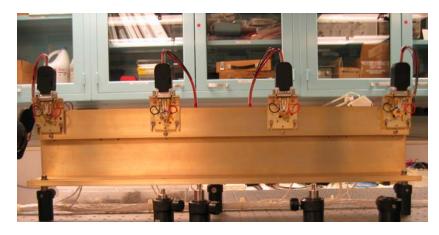


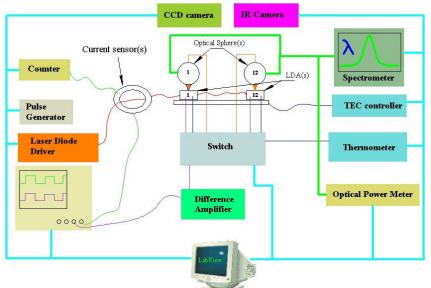
- Life tests
 - Power/temperature cycling
 - Test of different array sizes
 - Vacuum
- Radiation Tests (in collaboration with the Applied Physics Lab)
- Improved Characterization Measurements



LDA Life Test



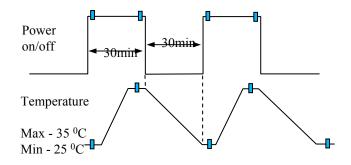




Total 12 diode will be tested

- •Constant temperature(25 °C) and constant power 2-G2 and 2-G4
- •Constant temperature and power ON/OFF cycling 2- G4
- •Constant power and temperature cycling (25-35 °C) 2- G4
- •Power ON/OFF cycling and temperature cycling 2-G2 and 2-G4

CYCLING PATTERN



- measurements (current, voltage, optical power, pulse counts)
- Infrared, near field images, and spectra will be taken weekly



Planned LDA Characterization Improvements

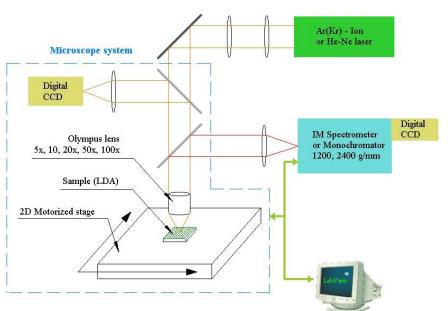


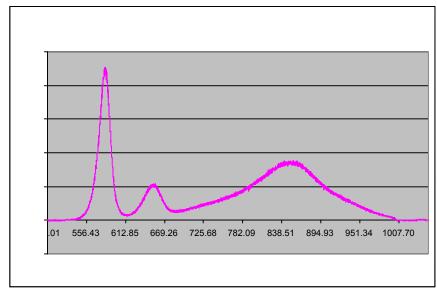
- Space resolved spectrum
- Space resolved optical power
- Time resolved spectrum
- Time resolved IR image
- Micro-photoluminescence spectroscopy



Micro Photoluminescence Spectroscopy









Conclusions



- Completed a good foundation for analysis of LDAs
- Continue to improve measurement capability
- Life tests begin soon
- Work has been focused on QCW 808 nm LDAs, the equipment could be used for other devices